



PRODUCT BULLETIN
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03 Oct 2007

SUBJECT: ON Semiconductor Product Bulletin #16056

TITLE: 60V Schottky Rectifier ESD Improvement & Datasheet High Temp Ir Limit Change

PROPOSED FIRST SHIP DATE: 03 Oct 2007

AFFECTED PRODUCT DIVISION: Rectifier Division

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor sales office or Ze Khai Lee < z.lee@onsemi.com >

NOTIFICATION TYPE:

ON Semiconductor considers this change approved unless specific conditions of acceptance are provided in writing. To do so, contact your local ON Semiconductor sales office.

DESCRIPTION AND PURPOSE:

This is to inform customers that ON Semiconductor will implement changes to the current process of the 60V Schottky rectifier devices to improve their ESD capabilities. This change will require ON Semiconductor to update the datasheet limits for the high temperature leakage (Ir) parameters.

For the 1A & 2A 60V devices, the high temperature leakage parameter (Ir) will be revised to 12mA.

For the 10A 60V devices, the high temperature leakage parameter (Ir) will be revised to 15mA.

For the 20A 60V devices, the high temperature leakage parameter (Ir) will be revised to 20mA.

AFFECTED DEVICE LIST

MBR1060
MBR1060G
MBR2060CT
MBR2060CTG
MBRA160T3
MBRA160T3G
MBRC1060WP
MBRS260T3
MBRS260T3G
NRVB1060
NRVB1060G
NRVB2060CTG
NRVBA160T3
NRVBA160T3G
NRVBS260T3G
SS26T3
SS26T3G